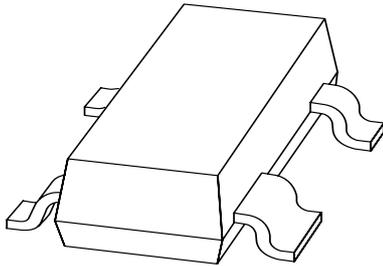


DATA SHEET



BCV61 NPN general purpose double transistor

Product data sheet
Supersedes data of 1997 Jun 16

1999 Apr 08

NPN general purpose double transistor

BCV61

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 30 V)
- Matched pairs.

APPLICATIONS

- For use in applications where the working point must be independent of temperature
- Current mirrors.

DESCRIPTION

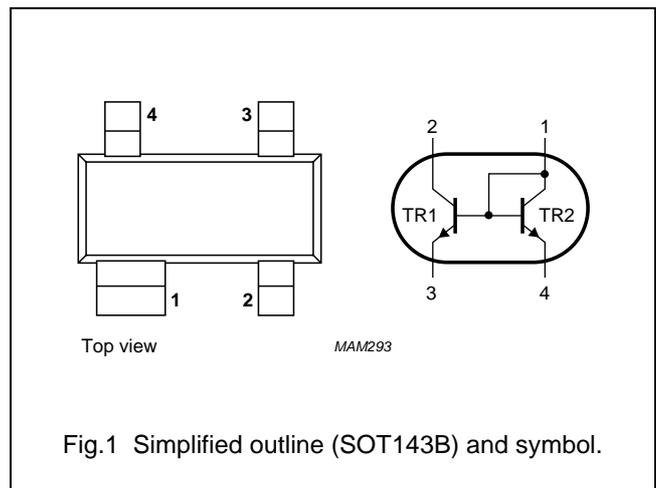
NPN double transistor in a SOT143B plastic package.
PNP complement: BCV62.

MARKING

TYPE NUMBER	MARKING CODE	TYPE NUMBER	MARKING CODE
BCV61	1Mp	BCV61B	1Kp
BCV61A	1Jp	BCV61C	1Lp

PINNING

PIN	DESCRIPTION
1	collector TR2; base TR1 and TR2
2	collector TR1
3	emitter TR1
4	emitter TR2



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage TR1	open emitter	–	30	V
V_{CEO}	collector-emitter voltage TR1	open base	–	30	V
V_{EBS}	emitter-base voltage	$V_{CE} = 0$	–	6	V
I_C	collector current (DC)		–	100	mA
I_{CM}	peak collector current		–	200	mA
I_{BM}	peak base current TR1		–	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Transistor TR1						
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 30\text{ V}$	–	–	15	nA
		$I_E = 0; V_{CB} = 30\text{ V}; T_j = 150\text{ °C}$	–	–	5	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	–	100	nA
h_{FE}	DC current gain	$I_C = 100\text{ }\mu\text{A}; V_{CE} = 5\text{ V}$	100	–	–	
		$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	110	–	800	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	90	250	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	–	200	600	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}; \text{note 1}$	–	700	–	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}; \text{note 1}$	–	900	–	mV
V_{BE}	base-emitter voltage	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}; \text{note 2}$	580	660	700	mV
		$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; \text{note 2}$	–	–	770	mV
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	2.5	–	pF
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure	$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 1\text{ kHz}; B = 200\text{ Hz}$	–	–	10	dB
Transistor TR2						
V_{EBS}	base-emitter forward voltage	$V_{CB} = 0; I_E = -250\text{ mA}$	–	–	-1.8	V
		$V_{CB} = 0; I_E = -10\text{ }\mu\text{A}$	-400	–	–	mV
h_{FE}	DC current gain	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	110	–	220	
			200	–	450	
			420	–	800	

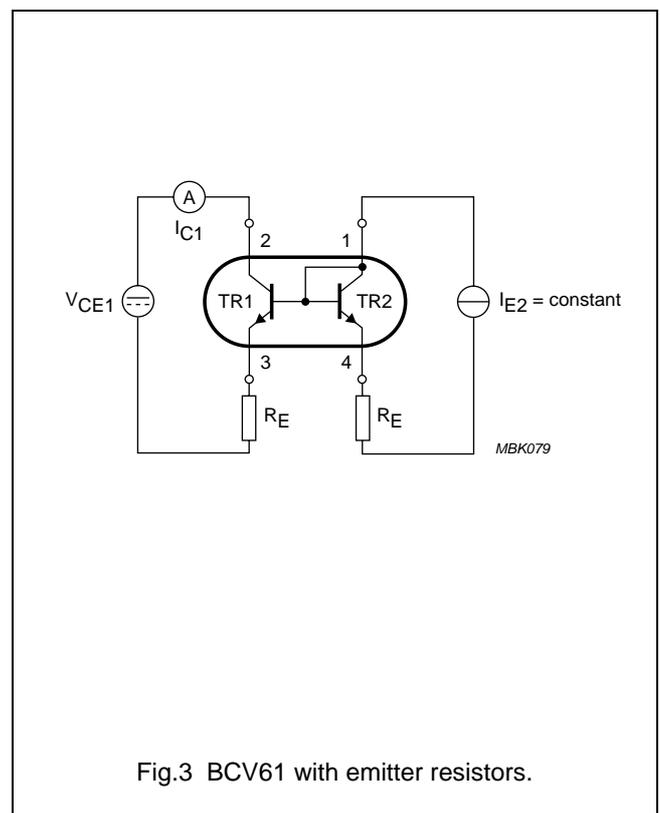
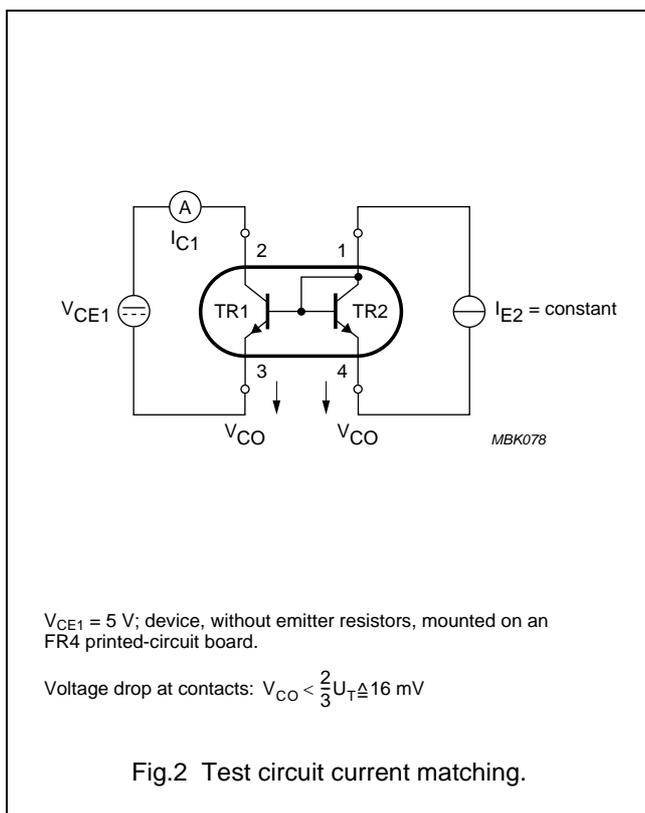
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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Transistors TR1 and TR2						
$\frac{I_{C1}}{I_{E2}}$	current matching of transistors TR1 and TR2	$I_{E2} = -0.5 \text{ mA}; V_{CE1} = 5 \text{ V}; T_{\text{amb}} \leq 25 \text{ }^\circ\text{C}$	0.7	–	1.3	
		$I_{E2} = -0.5 \text{ mA}; V_{CE1} = 5 \text{ V}; T_{\text{amb}} \leq 150 \text{ }^\circ\text{C}$	0.7	–	1.3	
I_{E2}	emitter current for thermal stability of I_{C1}	$V_{CE1} = 5 \text{ V}$; note 3; (see Fig.2)	–	–	–5	mA

Notes

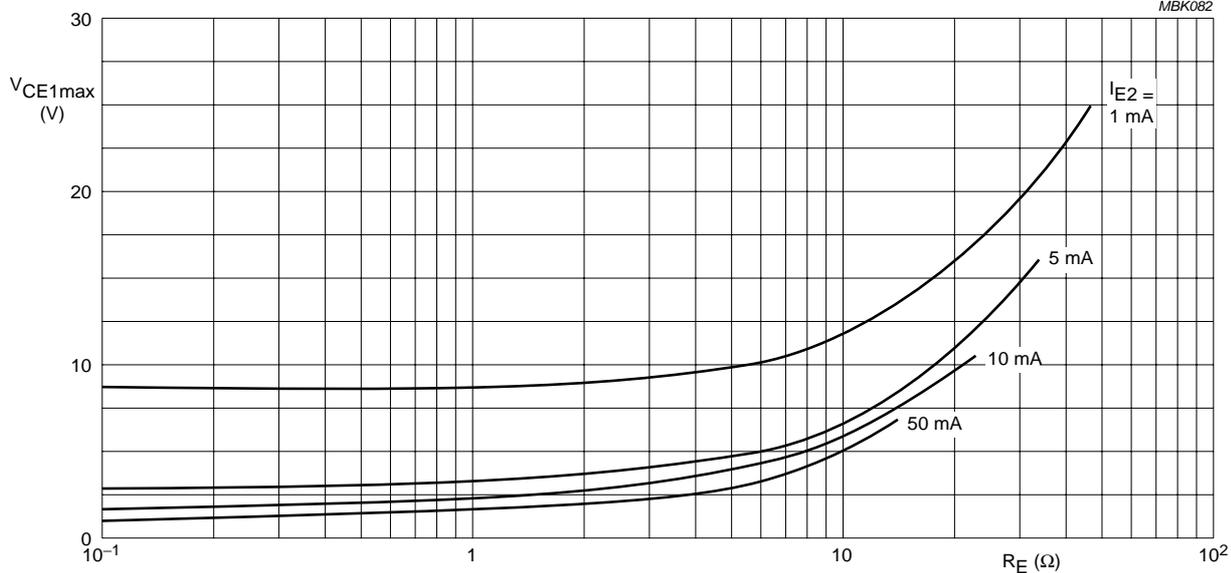
1. Decreasing 1.7 mV/°C with increasing temperature.
2. Decreasing 2 mV/°C with increasing temperature.
3. Device, without emitter resistors, mounted on an FR4 printed-circuit board.



NPN general purpose double transistor

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MBK082



$\frac{I_{C1}}{I_{E2}} = 1,3$ (see Fig.3).

Fig.4 Maximum collector-emitter voltage as a function of emitter resistance.

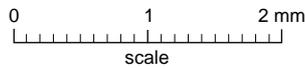
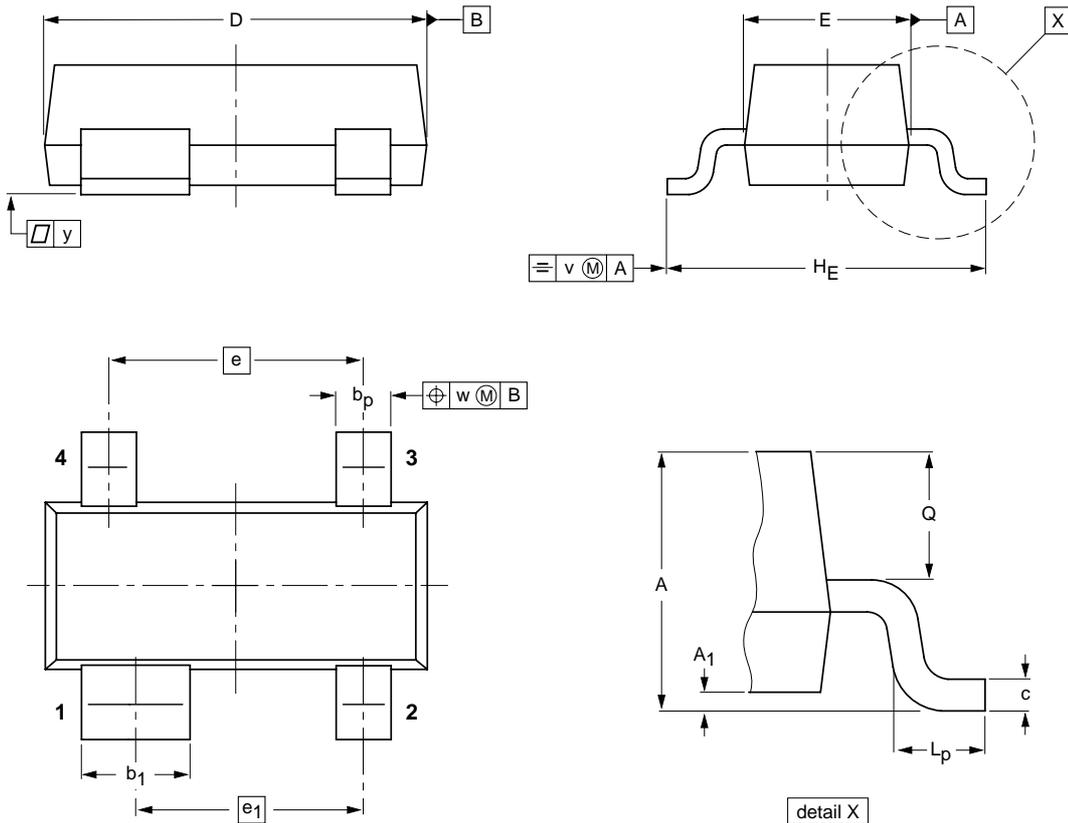
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PACKAGE OUTLINE

Plastic surface mounted package; 4 leads

SOT143B



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	b ₁	c	D	E	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.1 0.9	0.1	0.48 0.38	0.88 0.78	0.15 0.09	3.0 2.8	1.4 1.2	1.9	1.7	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT143B						97-02-28

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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